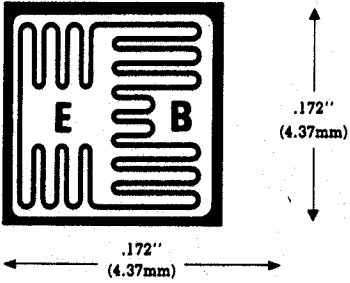


CHIP NUMBER

111



NPN EPI BASE POWER TRANSISTOR

CONTACT METALLIZATION

Base and emitter: > 50,000 Å Aluminum

Collector: Gold

(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL

Size: .375" Diameter (9.53mm)

Thickness: .020" (0.51mm)

BeO PEDESTAL

Size: .250" x .312" (6.35mm x 7.93mm)

Thickness: .042" (1.07mm)

ASSEMBLY RECOMMENDATIONS

It is advisable that:

a) the chip be eutectically mounted with gold silicon preform 98/2%.

b) 12 mil (0.305mm) aluminum wire be ultrasonically attached to the base and emitter contacts.

Base: .035" x .038" (0.89mm x 0.97mm)
Emitter: .036" x .060" (0.91mm x 1.52mm)

TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 111 in a TO-3 or equivalent case:

V _{CEO}	V _{CE(s)} @	I _C	I _B	h _{FE} @	I _C	V _{CE}
> 60V	< 4V	25A	6.25A	> 15	15A	5V
> 80V	< 4V	25A	6.25A	> 15	15A	5V

V _{CEO}	V _{CEX}	V _{EBO}	f _T	C _{OBO}	θ _{JC}
> 60V	60V	> 5V	3MHz	< 300pF	< 1.0°C/W
> 80V	80V	> 5V	3MHz	< 300pF	< 1.0°C/W

TYPICAL DEVICE TYPES: 2N3716, 2N5303, 2N5881, 2N5882

